

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) An electron beam exposure apparatus comprising:  
electron beam irradiation means,  
means for holding an irradiation-target substrate, and  
means for holding a 1:1 mask to be placed near said irradiation-target substrate  
between said electron beam irradiation means and said irradiation-target substrate, ~~said  
electron beam exposure apparatus characterized in that~~

wherein said means for holding said irradiation-target substrate and said means for  
holding said 1:1 mask hold said irradiation-target substrate and said 1:1 mask substantially  
vertical, respectively, and

wherein said 1:1 mask is a stencil mask which has a membrane and an island-like  
pattern.

2. (Currently Amended) An electron beam exposure apparatus according to  
claim 1, ~~characterized in that~~ wherein said means for holding said irradiation-target substrate  
and said means for holding said 1:1 mask keep said irradiation-target substrate and said 1:1  
mask substantially parallel to each other.

3. (Currently Amended) An electron beam exposure method for irradiating an  
electron beam from electron beam irradiation means onto an irradiation-target substrate  
through a 1:1 mask in a pattern determined by said 1:1 mask, ~~said electron beam exposure  
method characterized by~~

comprising:

preparing, as said 1:1 mask, a stencil mask which has a membrane and an island-like  
pattern;

arranging said irradiation-target substrate and said 1:1 mask substantially vertical,  
respectively; and

exposing the stencil mask with the island-like pattern on the irradiation-target substrate by one-time exposure.

4. (Canceled).

5. (Canceled).

6. (Currently Amended) A ~~semiconductor device manufacturing~~ method characterized in that ~~said irradiation-target substrate is~~ of manufacturing a semiconductor device by using the electron beam exposure apparatus according to claim 1, and by comprising:

preparing the semiconductor wafer as the irradiation-target substrate and preparing, as a 1:1 mask, a stencil mask which has a membrane and an island-like pattern; and at least a process of

exposing the island-like pattern of the stencil mask onto said semiconductor wafer by one-time exposure ~~by the use of the electron beam exposure apparatus according to claim 1 or~~ 2.

7. (Canceled).

8. (Currently Amended) An electron beam exposure apparatus comprising a 1:1 mask and an irradiation-target substrate arranged so as to face said 1:1 mask, ~~said electron beam exposure apparatus characterized in that~~ wherein said 1:1 mask and said irradiation-target substrate are arranged so as to be parallel to a gravity direction; and

wherein said 1:1 mask is formed by a stencil mask which has a membrane and an island-like pattern.

9. (New) An electron beam exposure apparatus according to claim 1, wherein the membrane is made of a diamond-like carbon material.

10. (New) An electron beam exposure apparatus according to claim 1, wherein the 1:1 mask is held by the means for holding to be within 10 microns of the irradiation-target substrate.